

Radiation Hardness Summary & Discussion

Thomas Tsang

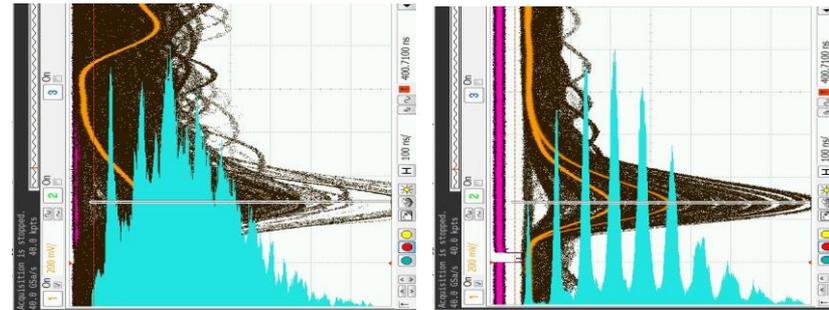
Brookhaven National Laboratory, Upton, NY 11973

ICASiPM, Schwetzingen, Germany, June 14, 2018

Summary

1. Neutron radiation and recovery studies on SiPMs, Thomas Tsang, BNL

Low dark current and excellent photon-number-resolving capability can be recovered by thermal annealing & found no significant difference when SiPMs are irradiated at room or in liquid nitrogen.

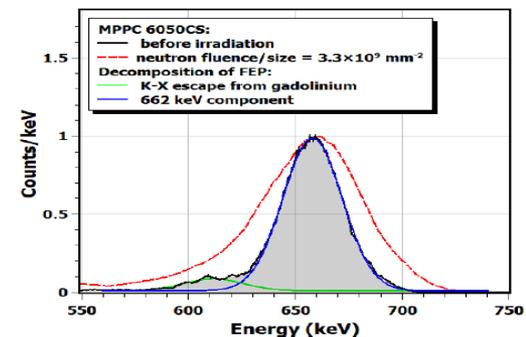


2. Investigation of a 10-Channel SiPM Module in a Neutron Beam, Vassily Kushpil, ASCR

Investigate the failure mechanism: structural, distortion E-field distribution and and to understand the radiation damage mechanism.

3. Study of Evolution of MPPC Properties Induced by Neutrons, Slawomir Mianowski, National Centre for Nuclear Research

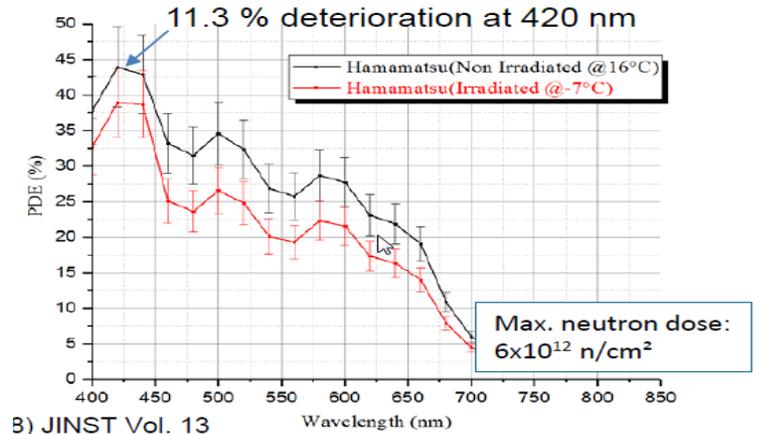
Extensive examination on the change of IV and V_{bd} , strong degradation of energy resolution, noise contribution to energy resolution.



Summary

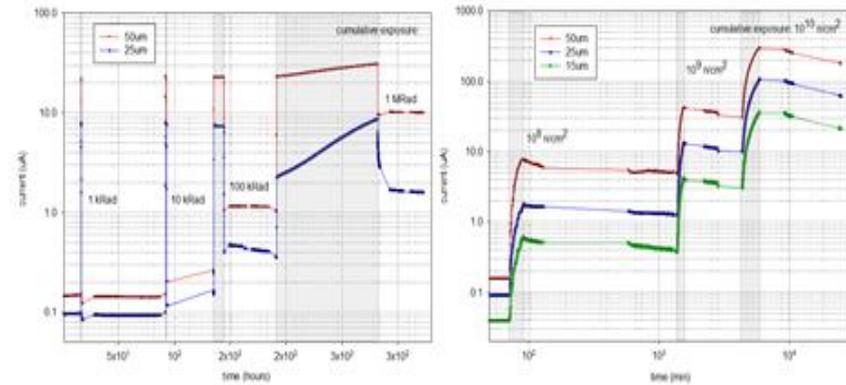
4. Assessment of Photodetection Performance of Analog and Digital SiPMs Exposed to .., Daniel Durini, FZ Jülich / INAOE

Investigated DCR, V_{bd} , PDE performances of analog and digital SiPMs, up to a dose of 6×10^{12} n/cm² and to understand the damage mechanisms: nuclear transmutation, point defect, generation of Frenkel pairs



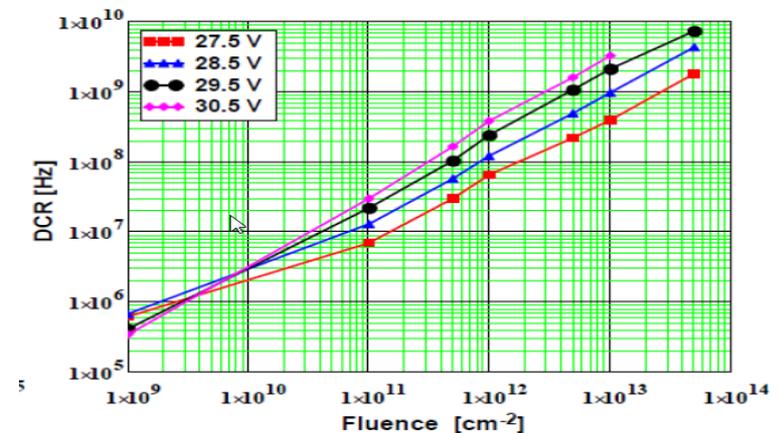
5. Effects of Neutron and Gamma Radiation on SiPMs, Sean Stoll, BNL

Gamma ray damage is similar to what is seen from neutron damage, but the level of damage is considerably less at comparable levels of exposure.



6. Characterization of Radiation Damaged SiPMs, Robert Klanner, Hamburg University

Develop & test methods to characterize hadron-damaged SiPMs and to understand the radiation damage mechanism.



Main effects of radiation damage

1. **Significant increase of dark current (DCR)**
2. **Loss of photon number resolving capability (PNR)**
3. Degradation of energy resolution δE_{n-pe}
4. SiPMs mostly operable but with much more noise
5. $<10^{12}$ n/cm², generally no significant change in V_{bd} , Gain, PDE, C_j , R_q
6. $>10^{12}$ n/cm², increase of afterpulse (more traps), loss of PDE (pixel too busy with excessive dark counts)
7. Timing performance of 1-pe to n-pe mostly degraded because of poor S/N ratio
8. Increase of power consumption - high dark current, self heating

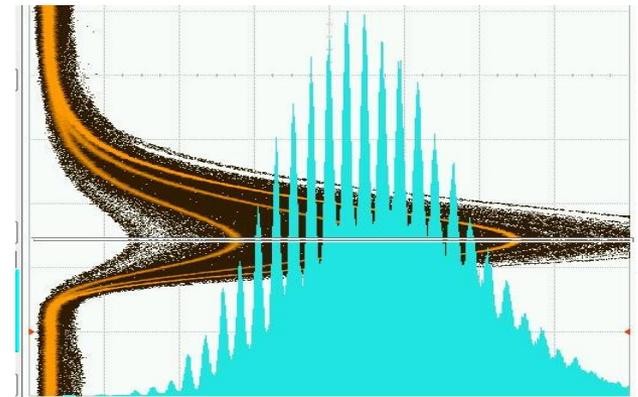
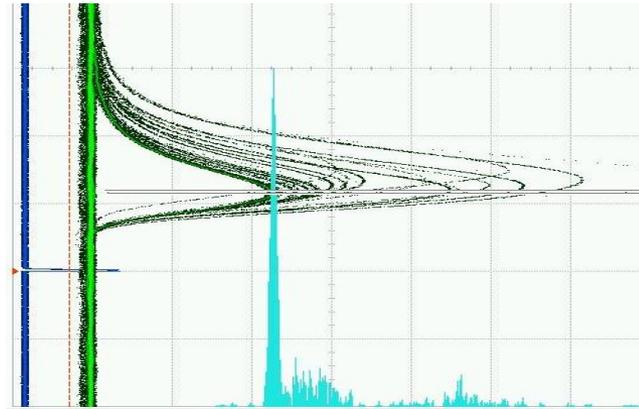
Hallmark of SiPM

Single photon sensitivity: single-photoelectron spectrum

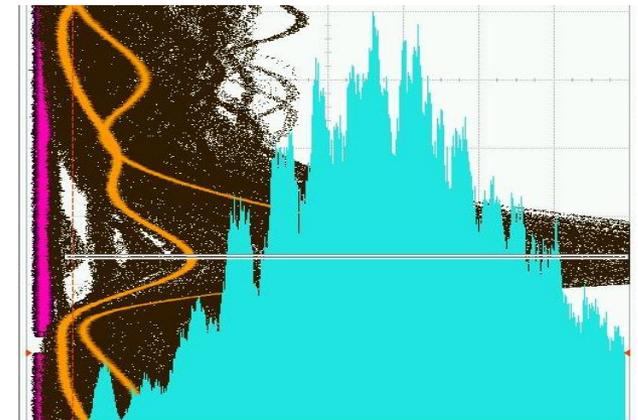
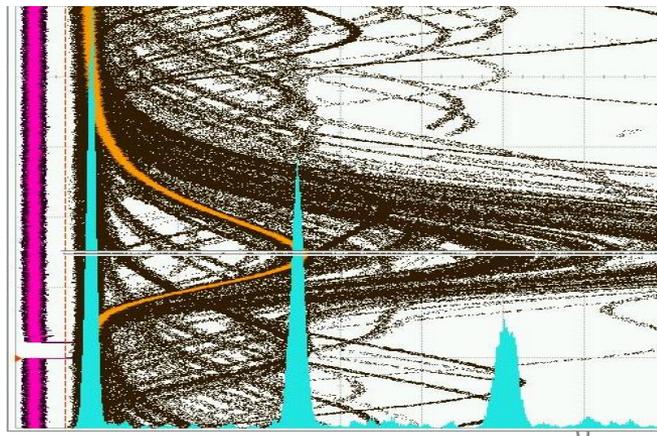
1-photoelectron

multi-photoelectron

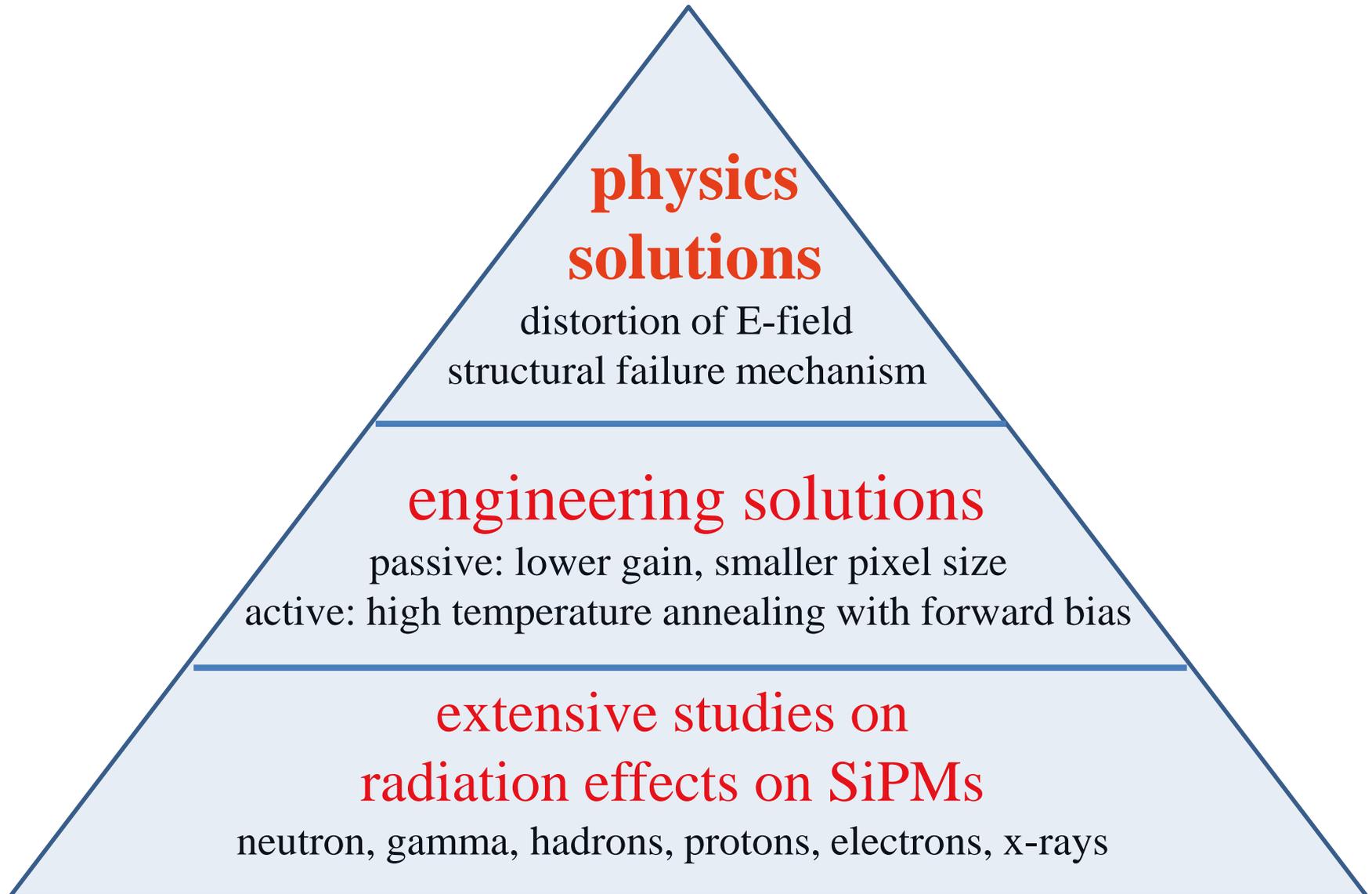
No
radiation



after
radiation



Approach on radiation hardening SiPM



Open for Discussion